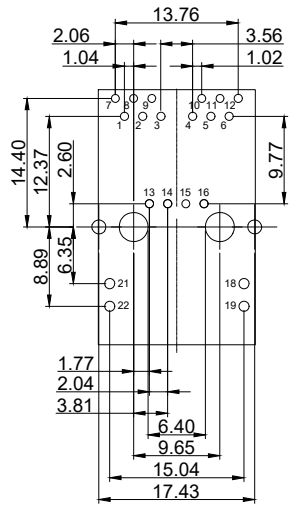
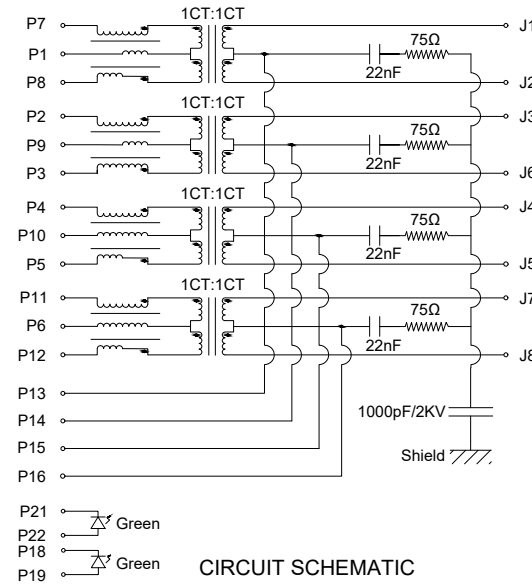
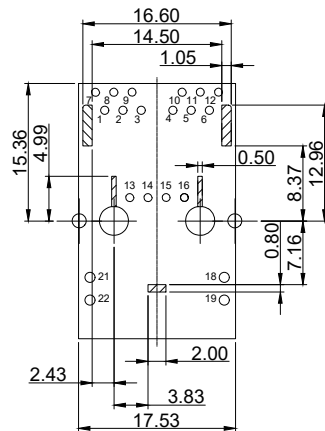
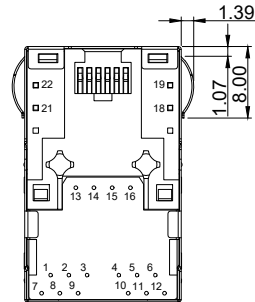


Housing: thermoplastic UL 94 V-0 black
 Contact: phosphor bronze, 30u Au plating over Ni plating in mating area, matte Sn plating over Ni plating in solder pin
 Shield: copper alloy Ni plating
 Operating temperature: 0°C~+70°C
 Storage temperature: -40°C~+85°C
 Insulation resistance: 500MΩ min.
 Mating/unmating force: 1.81KgF max.
 Durability: 750 cycles min.
 Contact resistance: 30mΩ
 Current rating: 0.1A max.
 Voltage rating: 48VDC max.
 Dielectric withstanding voltage: 2250 VDC contact to shield



RECOMMENDED PCB LAYOUT



CIRCUIT SCHEMATIC

PARAMETER	SPECIFICATIONS	
PRIMARY INDUCTANCE	120uH Min. @100KHz, 100mV	
INSERTION LOSS	100KHz	-3.0dB Max.
	1-400MHz	-2.0dB Max.
RETURN LOSS	1-100MHz	-22dB Min.
	100-500MHz	-22+ 20.75*LOG(f/100)
CROSS TALK	1-100MHz	-28dB Min.
	100-500MHz	-19dB Min.
COMMON MODE REJECTION RATIO	1-40MHz	-30dB Min.
	40-100MHz	-28dB Min.
COMM. TO DIFF. REJECTION RATIO	1-250MHz	-30dB Min.
	250-500MHz	-22dB Min.
INDUCTANCE	180uH Min. @100KHz	
ISOLATION	2250VDC FOR 60s	
CURRENT CARRYING CAPABILITY RJ45 P1~8	900mA max. @57V DC continuous	

		UNIT	mm
		REVISION	P1
PRODUCT		RJ45 1x1 ICM 10G PoE	
DWG NO.		PART NO.	
EZ111S-115ND21-02			
PROJECTION	SCALE	SHEET	1 OF 1
		TOLERANCES	
		.0 ± 0.38	
		.00 ± 0.20	
		.000 ± 0.10	
		0.° ± 2.0°	
		0.° ± 1.0°	